P-Channel Enhancement-Mode Vertical DMOS Power FETs

Ordering Information

BV_{DSS} / BV_{DGS}	$R_{DS(ON)}$ (max)	$I_{D(ON)}$ (min)	Order Number / Package			
			TO-39	TO-92	TO-220	DICE
-160V	25Ω	-250mA	VP0116N2	VP0116N3	VP0116N5	VP0116ND
-200V	25Ω	-250mA	VP0120N2	VP0120N3	VP0120N5	VP0120ND

Features

- ☐ Freedom from secondary breakdown
- ☐ Low power drive requirement
- ☐ Ease of paralleling
- ☐ Low C_{ISS} and fast switching speeds
- ☐ Excellent thermal stability
- ☐ Integral Source-Drain diode
- ☐ High input impedance and high gain
- ☐ Complementary N- and P-Channel devices

Advanced DMOS Technology

These enhancement-mode (normally-off) power transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and negative temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

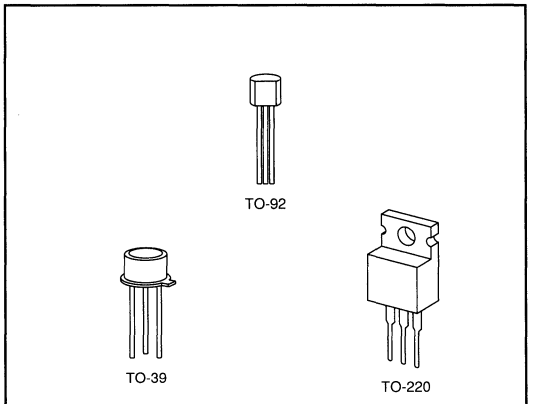
Supertex Vertical DMOS Power FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Applications

- ☐ Motor control
- ☐ Convertors
- ☐ Amplifiers
- ☐ Switches
- ☐ Power supply circuits
- ☐ Driver (Relays, Hammers, Solenoids, Lamps, Memories, Displays, Bipolar Transistors, etc.)

Package Options

(Note 1)



Note 1: See Package Outline section for discrete pinouts.

Absolute Maximum Ratings

Drain-to-Source Voltage	BV_{DSS}
Drain-to-Gate Voltage	BV_{DGS}
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

*Distance of 1.6 mm from case for 10 seconds.

Thermal Characteristics

Package	I_D (continuous)*	I_D (pulsed)*	Power Dissipation @ T_C = 25°C	θ_{ja} °C/W	θ_{jc} °C/W	I_{DR}	I_{DRM}*
TO-39	-0.2A	-0.65A	3.5W	125	35	-0.2A	-0.65A
TO-92	-0.1A	-0.35A	1.0W	170	125	-0.1A	-0.35A
TO-220	-0.425A	-1.0A	15.0W	70	8.3	-0.425A	-1.0A

* I_D (continuous) is limited by max rated T_j.

Electrical Characteristics (@ 25°C unless otherwise specified)

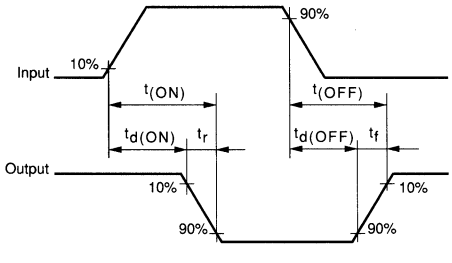
(Notes 1 and 2)

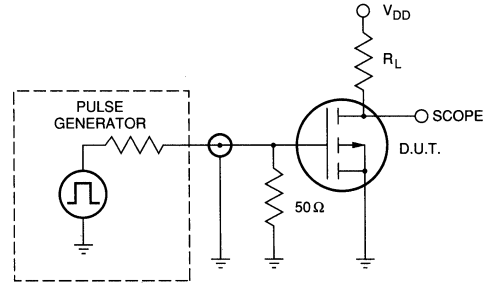
Symbol	Parameter		Min	Typ	Max	Unit	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	VP0120	-200			V	I_D = -1.0mA, V_{GS} = 0
		VP0116	-160				
$V_{GS(th)}$	Gate Threshold Voltage		-1.5		-3.5	V	V_{GS} = V_{DS}, I_D = -1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature			-6.0		mV/°C	I_D = -1.0mA, V_{GS} = V_{DS}
I_{GSS}	Gate Body Leakage				-100	nA	V_{GS} = ±20V, V_{DS} = 0
I_{DSS}	Zero Gate Voltage Drain Current				-10	µA	V_{GS} = 0, V_{DS} = Max Rating
					-1	mA	V_{GS} = 0, V_{DS} = 0.8 Max Rating, T_A = 125°C
$I_{D(ON)}$	ON-State Drain Current		-100	-400		mA	V_{GS} = -5V, V_{DS} = -25V
			-350	-700			V_{GS} = -10V, V_{DS} = -25V
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance			25	40	Ω	V_{GS} = -5V, I_D = -50mA
				15	25		V_{GS} = -10V, I_D = -100mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature			0.6		%/°C	I_D = -100mA, V_{GS} = -10V
G_{FS}	Forward Transconductance		50	70		m℧	V_{DS} = -25V, I_D = -100mA
C_{ISS}	Input Capacitance			50	60	pF	V_{GS} = 0, V_{DS} = -25V, f = 1 MHz
C_{OSS}	Common Source Output Capacitance			20	30		
C_{RSS}	Reverse Transfer Capacitance			5	10		
$t_{d(ON)}$	Turn-ON Delay Time			4	10	ns	V_{DD} = -25V, I_D = -100mA, R_S = 50Ω
t_r	Rise Time			4	10		
$t_{d(OFF)}$	Turn-OFF Delay Time			4	10		
t_f	Fall Time			4	10		
V_{SD}	Diode Forward Voltage Drop			1.0		V	I_{SD} = -0.5A, V_{GS} = 0
t_{rr}	Reverse Recovery Time			500		ns	I_{SD} = -0.5A, V_{GS} = 0

Note 1: All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

Note 2: All A.C. parameters sample tested.

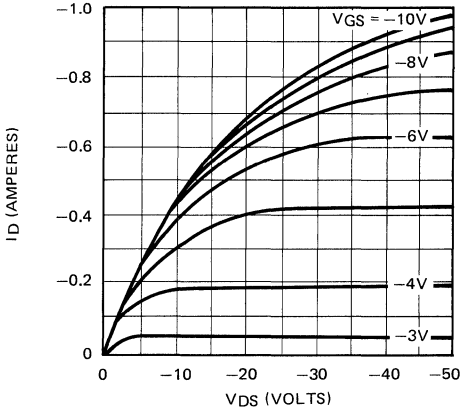
Switching Waveforms and Test Circuit



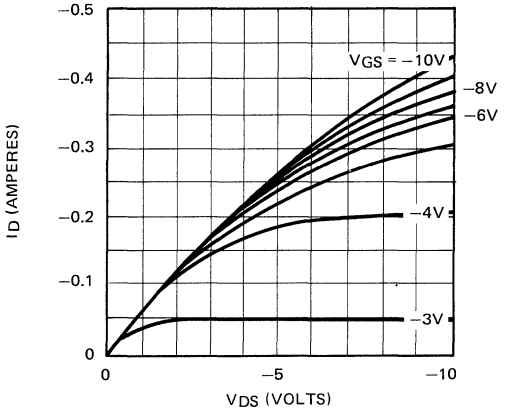


Typical Performance Curves

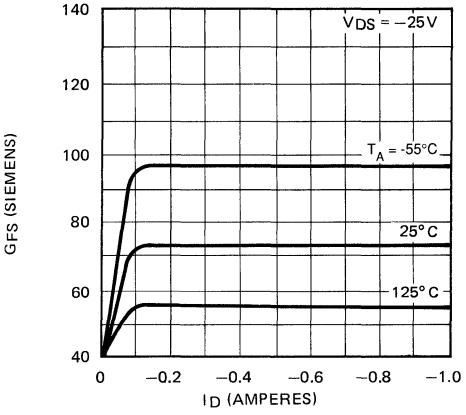
Output Characteristics



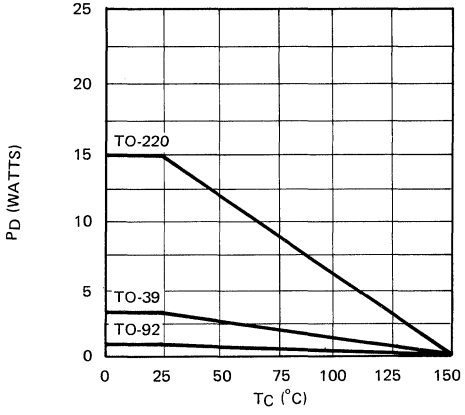
Saturation Characteristics



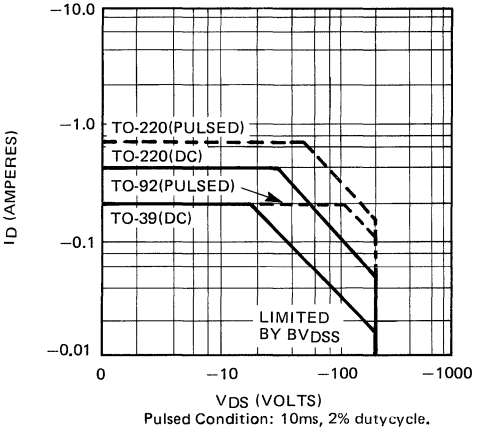
Transconductance Vs. Drain Current



Power Dissipation Vs. Case Temperature

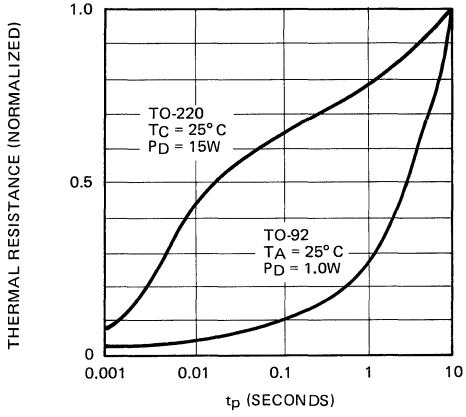


Maximum Rated Safe Operating Area

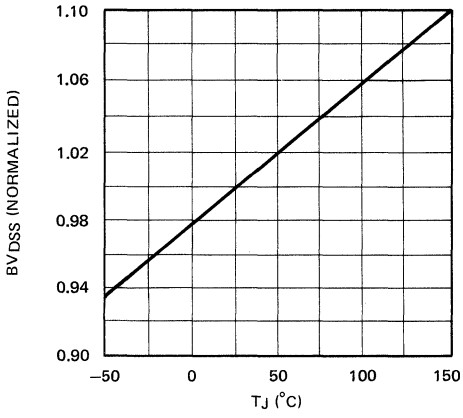


Pulsed Condition: 10ms, 2% dutycycle.

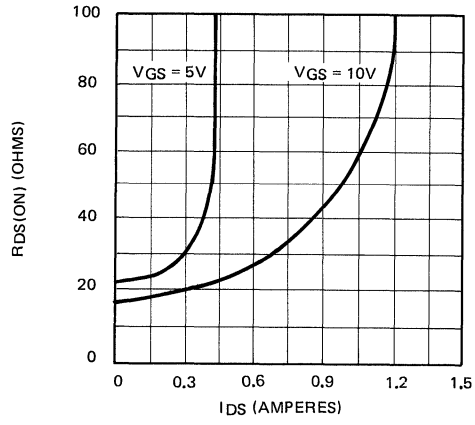
Thermal Response Characteristics



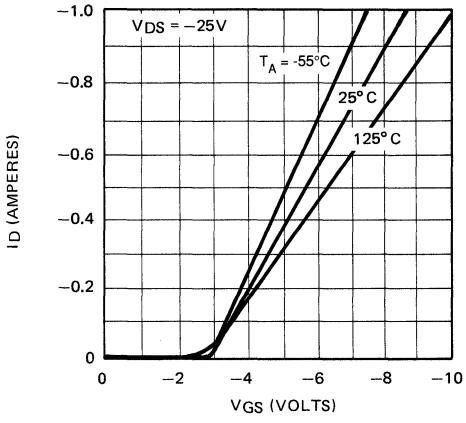
BVDSS Variation with Temperature



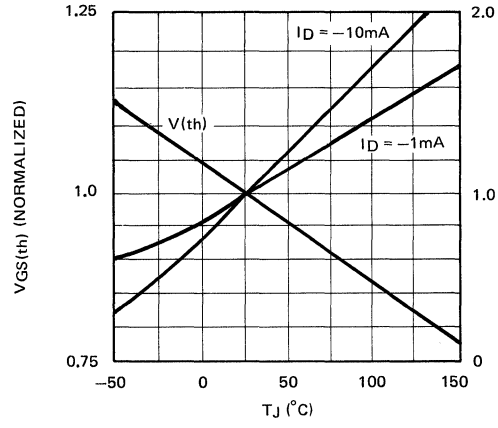
ON - Resistance Vs .Drain Current



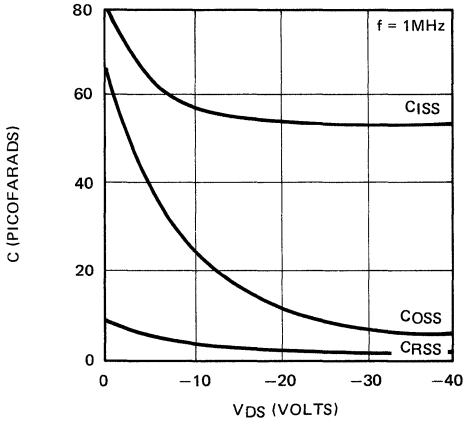
Transfer Characteristics



V(th) and RDS Variation with Temperature



Capacitance Vs. Drain-to-Source Voltage



Gate Drive Dynamic Characteristics